SLOS082A - D2484, MARCH 1979 - REVISED JANUARY 1993

- Low Input Offset Voltage . . . 0.5 mV Max
- Low Power Consumption
- Wide Common-Mode and Differential Voltage Ranges
- Low Input Bias and Offset Currents
- High Input Impedance . . . JFET-Input Stage
- Internal Frequency Compensation
- Latch-Up-Free Operation
- High Slew Rate . . . 18 V/μs Typ
- Low Total Harmonic Distortion 0.003% Typ

description

These JFET-input operational amplifiers incorporate well-matched high-voltage JFET and bipolar transistors in a monolithic integrated circuit. They feature low input offset voltage, high slew rate, low input bias and offset currents, and low temperature coefficient of input offset voltage. Offset-voltage adjustment is provided for the TL087 and TL088.

The C-suffix devices are characterized for operation from 0° C to 70° C, and the I-suffix devices are characterized for operation from -40° C to 85° C. The M-suffix devices are characterized for operation over the full military temperature range of -55° C to 125° C.

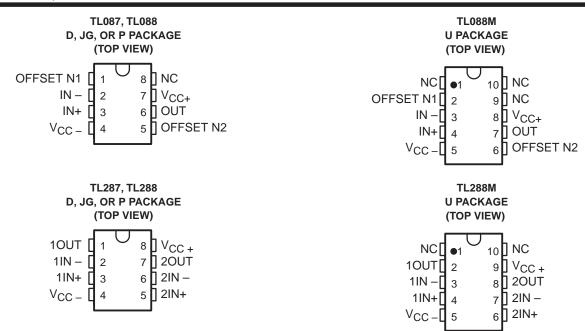
AVAILABLE OPTIONS

		Via may		PACK	AGE	
TA	TYPE	V _{IO} max AT 25°C	SMALL OUTLINE (D)	CERAMIC DIP (JG)	PLASTIC DIP (P)	FLAT (U)
0°C to	Single	0.5 mV 1 mV	TL087CD TL088CD	TL087CJG TL088CJG	TL087CP TL088CP	
70°C	Dual	0.5 mV 1 mV	TL287CD TL288CD	TL287CJG TL288CJG	TL287CP TL288CP	
−40°C to	Single	0.5 mV 1 mV	TL087ID TL088ID	TL087IJG TL088IJG	TL087IP TL088IP	
85°C	Dual	0.5 mV 1 mV	TL287ID TL288ID	TL287IJG TL288IJG	TL287IP TL288IP	
−55°C to	Single	1 mV		TL088MJG		TL088MU
125°C	Dual	1 mV		TL288MJG		TL288MU

The D package is available taped and reeled. Add the suffix R to the device type (e.g., TL087CDR).

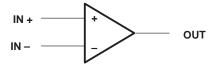


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NC - No internal connection

symbol (each amplifier)



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

		TL088M TL288M	TL087I TL088I TL287I TL288I	TL087C TL088C TL287C TL288C	UNIT		
Supply voltage, VCC+ (see Note 1)		18	18	18	V		
Supply voltage, V _{CC} - (see Note 1)		-18	-18	-18	V		
Differential input voltage (see Note 2)		±30	±30	±30	V		
Input voltage (see Notes 1 and 3)		±15	±15	±15	V		
Input current, I _I (each Input)	±1	±1	±1	mA			
Output current, IO (each output)	Output current, IO (each output)			±80	mA		
Total V _{CC} + terminal current		160	160	160	mA		
Total V _{CC} - terminal current		-160	-160	-160	mA		
Duration of output short circuit (see Note 4)		unlimited unlimited unlimit					
Continuous total dissipation		See Dissipation Rating Table					
Operating free-air temperature range		-55 to 125	-25 to 85	0 to 70	°C		
Storage temperature range	-65 to 150 -65 to 150		-65 to 150	°C			
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds	JG or U package	300	300	300	°C		
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	D or P package		260	260	°C		

- NOTES: 1. All voltage values, except differential voltages, are with respect to the midpoint between V_{CC+} and V_{CC-}.
 - 2. Differential voltages are at the noninverting input terminal with respect to the inverting input terminal.
 - 3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.
 - 4. The output may be shorted to ground or to either supply. Temperature and/or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{\scriptsize A}} \le 25^{\circ}\mbox{\scriptsize C}$ POWER RATING	DERATING FACTOR ABOVE T _{A =} 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW	377 mW	N/A
JG	1050 mW	8.4 mW/°C	672 mW	546 mW	210 mW
Р	1000 mW	8.0 mW/°C	640 mW	520 mW	N/A
U	675 mW	5.4 mW/°C	432 mW	351 mW	135 mW

recommended operating conditions

		C-SUFFIX		I-SUFFIX			M-SUFFIX			UNIT	
		MIN	NOM	MAX	MIN	NOM	MAX	MIN	NOM	MAX	UNIT
Supply voltage, V _{CC}		±5		±5	±5		±5	±5		±15	V
Common mode input voltage Vie	$V_{CC\pm} = \pm 5 \text{ V}$	-1		4	-1		4	-1		4	V
Common-mode input voltage, V _{IC}	$V_{CC\pm} = \pm 15 \text{ V}$	-11		11	-11		11	-11		11	V
Input voltage V	$V_{CC\pm} = \pm 5 \text{ V}$	-1		4	-1		4	-1		4	V
Input voltage, V _I	$V_{CC\pm} = \pm 15 \text{ V}$	-11		11	-11		11	-11		11	V
Operating free-air temperature, TA		0		70	-40		85	-55		125	°C



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electrical characteristics, $V_{CC\pm} = \pm 15 \text{ V}$

	PARAMETER	TEST C	onditions†		ΓL088M ΓL288M] :	TL087I TL088I TL287I TL288I		1	L087C L088C L287C L288C		UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
		$R_S = 50 \Omega$,	TL087, TL287					0.1	0.5		0.1	0.5	
.,	land Marked a	$V_O = 0$ $T_A = 25^{\circ}C$	TL088, TL288		0.1	3		0.1	1		0.1	1	
VIO	Input offset voltage	$R_S = 50 \Omega$,	TL087, TL287						2			1.5	mV
		$V_O = 0$, $T_A = \text{full range}$	TL088, TL288			6			3			2.5	
$\alpha_{ extsf{VIO}}$	Temperature coefficient of input offset voltage	$R_S = 50 \Omega$,	$T_A = 25$ °C to MAX		10			8			8		μV/°C
li o	Input offset current	T _A = 25°C			5			5	100		5	100	рА
lio	Input offset current	T _A = full range				25			3			2	nA
I _{IB}	Input bias current [‡]	T _A = 25°C			30			30	200		30	200	рА
		T _A = full range				100			20			7	nA
VICR	Common-mode input voltage range	T _A = 25°C		VCC-+	:0		VCC-+	0		VCC-+ to VCC+-			V
		T _A = 25°C,	R _L = 10 kΩ	24	27		24	27		24	27		
V _{O(PP)}	Maximum-peak-to-peak output voltage swing	T _A = full range	$R_{L} \ge 10 \text{ k}\Omega$ $R_{L} \ge 2 \text{ k}\Omega$	24 20			24 20			24 20			V
AVD	Large-signal differential	$R_L \ge 2 k\Omega$, $T_A = 25^{\circ}C$	$V_0 = \pm 10 \text{ V},$	50	105		50	105		50	105		V/mV
۸۷۵	voltage amplification	$R_L \ge 2 \text{ k}\Omega,$ $T_A = \text{full range}$	$V_0 = \pm 10 \text{ V},$	25			25			25			V/111V
B ₁	Unity-gain bandwidth	T _A = 25°C			3			3			3		MHz
rį	Input resistance	T _A = 25°C			1012			1012			1012		Ω
CMRR	Common–mode rejection ratio	$R_S = 50 \Omega$, $V_{IC} = V_{ICR} min$		80	93		80	93		80	93		dB
ksvr	Supply voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	$R_S = 50 \Omega$, $V_{CC\pm} = \pm 9 V \text{ to}$ $T_A = 25^{\circ}\text{C}$		80	99		80	99		80	99		dB
lcc	Supply current (per amplifier)	No load, T _A = 25°C	V _O = 0 V,		26	2.8		2.6	2.8		2.6	2.8	mA

[†] All characteristics are measured under open–loop conditions with zero common-mode input voltage unless otherwise specified. Full range for T_A is –55°C to 125°C for TL_88M; –40°C to 85°C for TL_8_I; and 0°C to 70°C for TL_8_C.
‡ Input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive. Pulse techniques must be used that will maintain

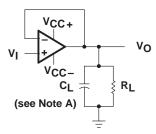


the junction temperature as close to the ambient temperature as possible.

operating characteristics $V_{CC}=\pm 15~V,\, T_A=25^{\circ}C$

PARAMETER		TEST C	TEST CONDITIONS			TL088M, TL288M			TL087I, TL087C TL088I, TL088C		
				MIN	TYP	MAX	MIN	TYP	MAX		
SR	Slew rate at unity gain	V _I = 10 V, C _L = 100 pF,	$R_L = 2 k\Omega$, $A_{VD} = 1$		18		8	18		V/μs	
t _r	Rise time	V _I = 20 mV,	$R_L = 2 k\Omega$,		55			55		ns	
	Overshoot factor	$C_L = 100 pF$,	$A_{VD} = 1$		25%			25%			
٧n	Equivalent input noise voltage	$R_S = 100 \Omega$,	f = 1 kHz		19			19		nV/√ Hz	

PARAMETER MEASUREMENT INFORMATION



NOTE A: C_L includes fixture capacitance.

Figure 1. Slew Rate, Rise/Fall Time, and Overshoot Test Circuit

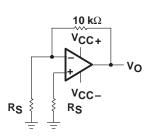


Figure 3. Noise Voltage Test Circuit

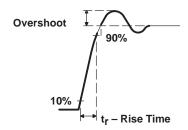
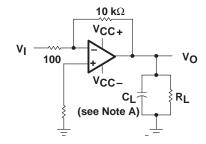


Figure 2. Rise Time and Overshoot Waveform



NOTE A: CL includes fixture capacitance.

Figure 4. Unity-Gain Brandwidth and Phase Margin Test Circuit

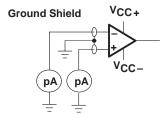


Figure 5. Input Bias and Offset Current Test Circuit

TL087, TL088, TL287, TL288 JFET-INPUT OPERATIONAL AMPLIFIERS

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typical values

Typical values as presented in this data sheet represent the median (50% point) of device parametric performance.

input bias and offset current

At the picoamp bias current level typical of these JFET operational amplifiers, accurate measurement of the bias current becomes difficult. Not only does this measurement require a picoammeter, but test socket leakages can easily exceed the actual device bias currents. To accurately measure these small currents, Texas Instruments uses a two-step process. The socket leakage is measured using picoammeters with bias voltages applied, but with no device in the socket. The device is then inserted in the socket and a second test that measures both the socket leakage and the device input bias current is performed. The two measurements are then subtracted algebraically to determine the bias current of the device.



TYPICAL CHARACTERISTICS

table of graphs

			FIGURE
αVIO	Temperature coefficient of input offset voltage	Distribution	6, 7
IIO	Input offset current	vs Temperature	8
IIB	Input bias current	vs V _{IC} vs Temperature	9 8
٧I	Common-mode input voltage range limits	vs V _{CC} vs Temperature	10 11
V _{ID}	Differential input voltage	vs Output voltage	12
VOM	Maximum peak output voltage swing	vs V _{CC} vs Output current vs Frequency vs Temperature	13 17 14, 15, 16 18
A _{VD}	Differential voltage amplification	vs R _L vs Frequency vs Temperature	19 20 21
z _O	Output impedance	vs Frequency	24
CMRR	Common-mode rejection ratio	vs Frequency vs Temperature	22 23
ksvr	Supply-voltage rejection ratio	vs Temperature	25
los	Short-circuit output current	vs V _{CC} vs Time vs Temperature	26 27 28
lcc	Supply current	vs V _{CC} vs Temperature	29 30
SR	Slew rate	vs R _L vs Temperature	31 32
	Overshoot factor	vs C _L	33
Vn	Equivalent input noise voltage	vs Frequency	34
THD	Total harmonic distortion	vs Frequency	35
B ₁	Unity-gain bandwidth	vs V _{CC} vs Temperature	36 37
фm	Phase margin	vs V _{CC} vs C _L vs Temperature	38 39 40
	Phase shift	vs Frequency	20
	Pulse response	Small-signal Large-signal	41 42

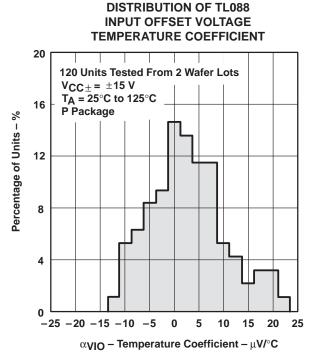
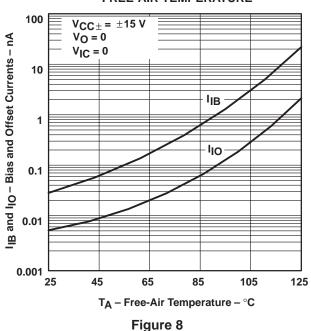


Figure 6

INPUT BIAS CURRENT AND INPUT OFFSET CURRENT vs FREE-AIR TEMPERATURE



DISTRIBUTION OF TL288 INPUT OFFSET VOLTAGE TEMPERATURE COEFFICIENT

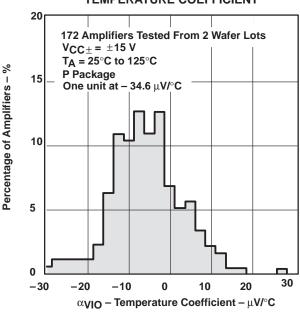
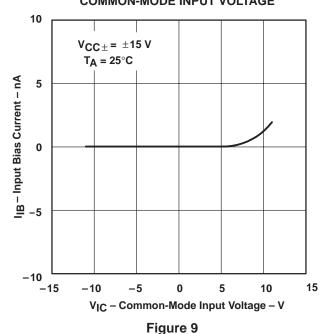


Figure 7

INPUT BIAS CURRENT vs COMMON-MODE INPUT VOLTAGE



† Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.



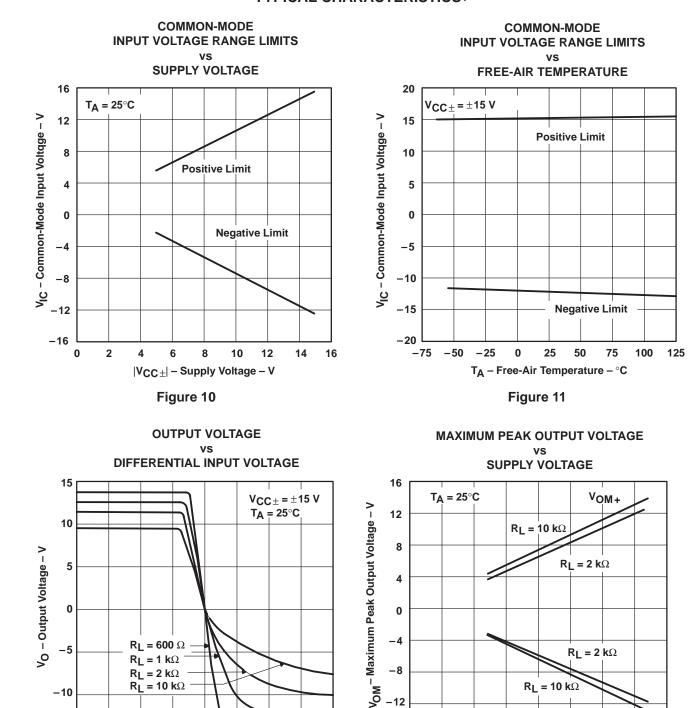


Figure 12 Figure 13

400

† Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.

 $R_L = 2 k\Omega$ $R_L = 10 \text{ k}\Omega$

0

V_{ID} - Differential Input Voltage - μV

200

-200

-10

-400



-8

12

-16

0

2

16

۷ом

10

 $|V_{CC\pm}|$ – Supply Voltage – V

MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE FREQUENCY 30 VO(PP) - Maximum Peak-to-Peak Output Voltage - V $R_L = 2 k\Omega$ $V_{CC\pm} = \pm 15 \text{ V}$ 25 20 15 T_A = 125°C 10 $V_{CC\pm} = \pm 5 \text{ V}$ -55°C 5 10 k 100 k 1 M 10 M

Figure 14

f - Frequency - Hz

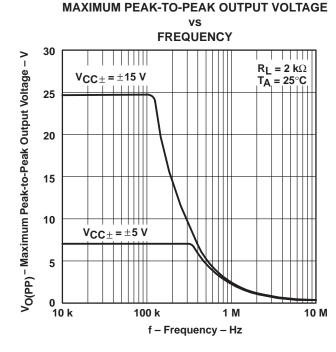
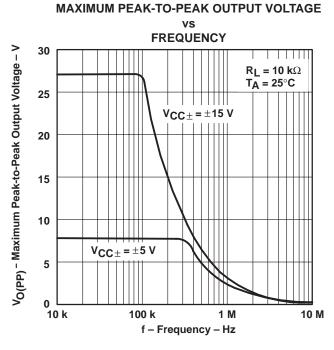
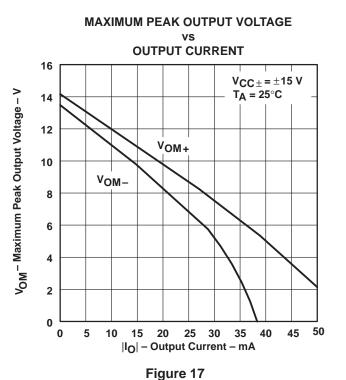


Figure 15







[†] Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.



MAXIMUM PEAK OUTPUT VOLTAGE FREE-AIR TEMPERATURE 16 $R_L = 10 k\Omega$ V_{OM} – Maximum Peak Output Voltage – V 12 VOM+ $R_L = 2 k\Omega$ 8 4 $V_{CC\pm} = \pm 15 V$ 0 -4 -8 VOM- $R_L = 2 k\Omega$ -12 $R_I = 10 k\Omega$ -16 75 -50-2525 50 100 125 T_A - Free-Air Temperature - °C

Figure 18

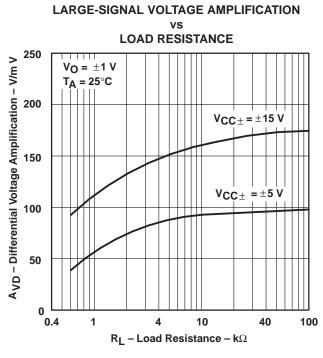


Figure 19

LARGE-SIGNAL DIFFERENTIAL VOLTAGE **AMPLIFICATION AND PHASE SHIFT**

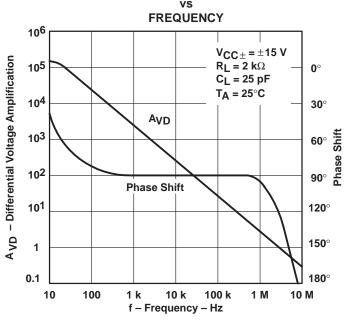


Figure 20

LARGE-SIGNAL VOLTAGE AMPLIFICATION

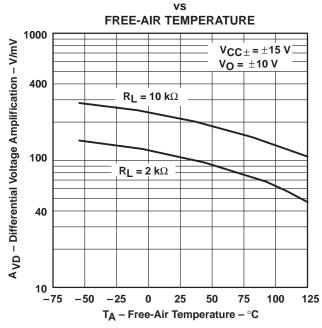


Figure 21

[†] Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.



COMMON-MODE REJECTION RATIO FREQUENCY 100 CMRR - Common-Mode Rejection Ratio - dB $V_{CC\pm} = \pm 15 \text{ V}$ 90 T_A = 25°C 80 70 60 50 40 30 20 10 100 10 k 100 k 1 M 10 M 10 f - Frequency - Hz

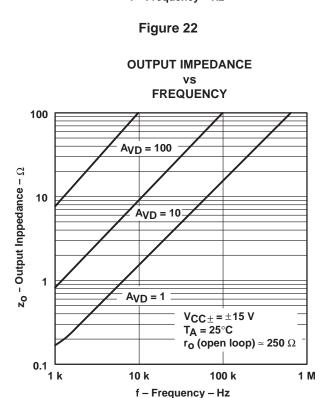


Figure 24

COMMON-MODE REJECTION RATIO FREE-AIR TEMPERATURE 100 CMRR - Common-Mode Rejection Ratio - dB VIC = VICR min 95 $V_{CC\pm} = \pm 15 V$ 90 85 $V_{CC\pm} = \pm 5 V$ 80 75 70 -50 25 50 75 100 125

Figure 23

 T_A – Free-Air Temperature – $^{\circ}$ C

SUPPLY-VOLTAGE REJECTION RATIO vs FREE-AIR TEMPERATURE

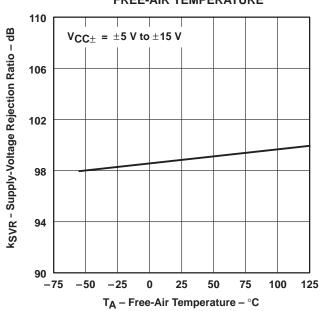


Figure 25

[†] Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.



SHORT-CIRCUIT OUTPUT CURRENT **SUPPLY VOLTAGE** 60 $V_O = 0$ Ios - Short-Circuit Output Current - mA $T_A = 25^{\circ}C$ 40 $V_{ID} = 1 V$ 20 0 -20 $V_{ID} = -1 V$ -60 2 10 12 14 16 $|V_{CC\pm}|$ – Supply Voltage – V

Figure 26

SHORT-CIRCUIT OUTPUT CURRENT

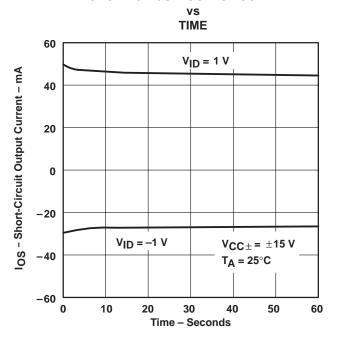


Figure 27

SHORT-CIRCUIT OUTPUT CURRENT

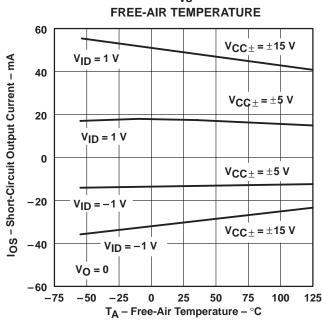
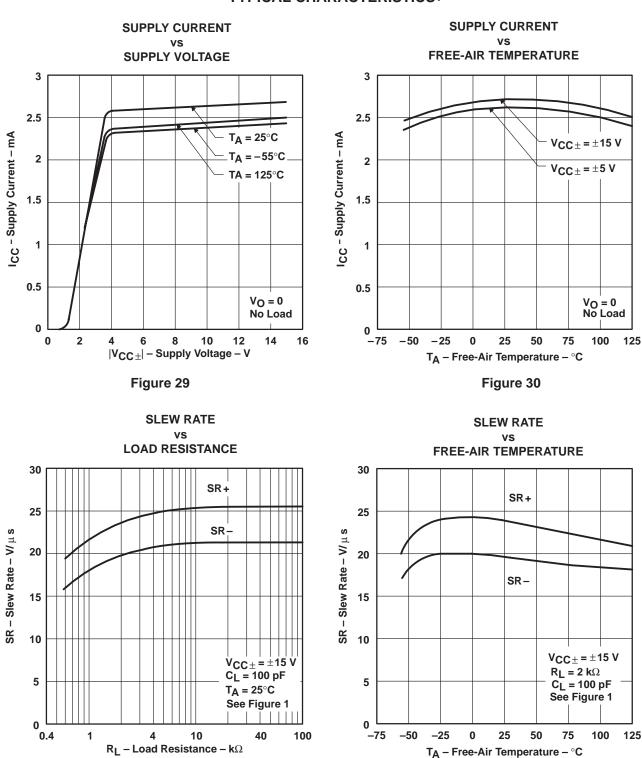


Figure 28

[†] Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.





[†] Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.

Figure 31



Figure 32

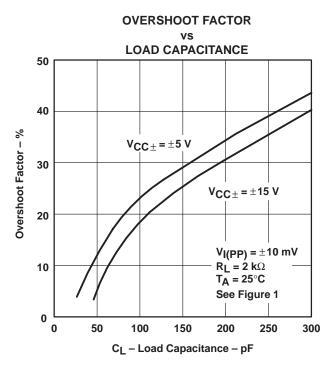


Figure 33

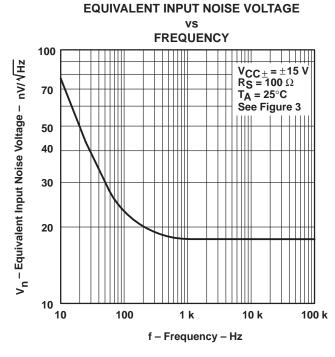
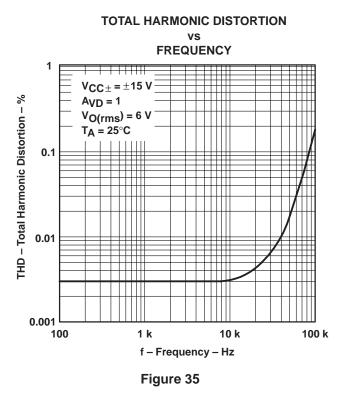
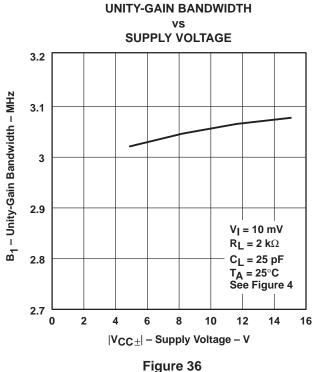


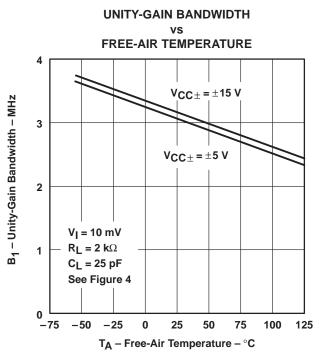
Figure 34





[†] Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.





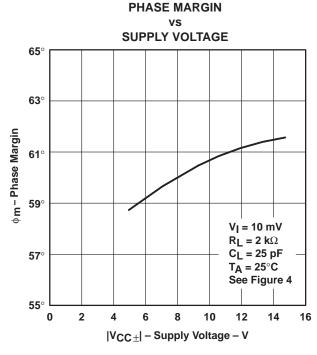
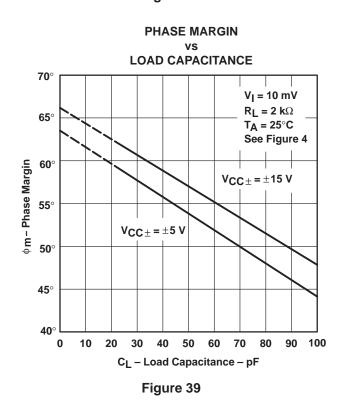
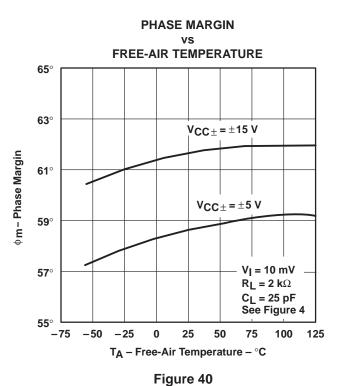


Figure 37



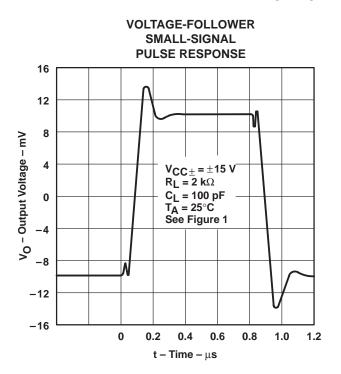




† Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS



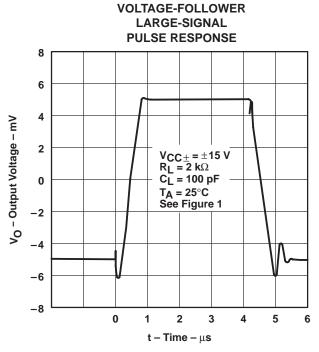


Figure 41

Figure 42

TYPICAL APPLICATION DATA

output characteristics

All operating characteristics are specified with 100-pF load capacitance. These amplifiers will drive higher capacitive loads; however, as the load capacitance increases, the resulting response pole occurs at lower frequencies, thereby causing ringing, peaking, or even oscillation. The value of the load capacitance at which oscillation occurs varies with production lots. If an application appears to be sensitive to oscillation due to load capacitance, adding a small resistance in series with the load should alleviate the problem. Capacitive loads of 1000 pF and larger may be driven if enough resistance is added in series with the output (see Figure 43).

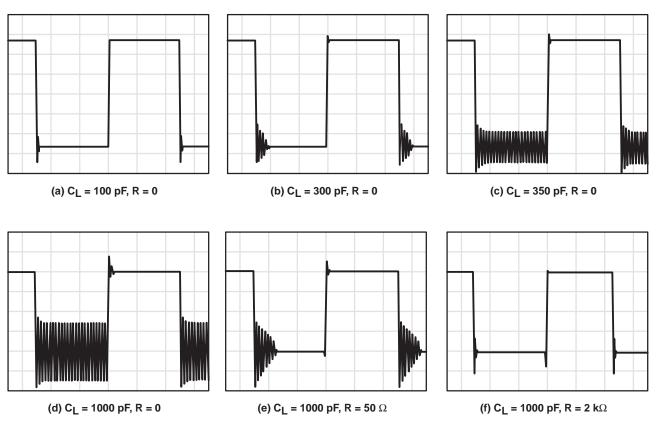


Figure 43. Effect of Capacitive Loads

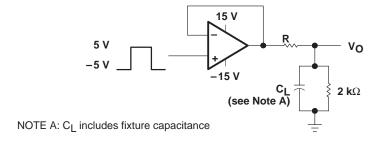


Figure 44. Test Circuit for Output Characteristics



TYPICAL APPLICATION DATA

input characteristics

These amplifiers are specified with a minimum and a maximum input voltage that, if exceeded at either input, could cause the device to malfunction.

Because of the extremely high input impedance and resulting low bias current requirements, these amplifiers are well suited for low-level signal processing; however, leakage currents on printed circuit boards and sockets can easily exceed bias current requirements and cause degradation in system performance. It is good practice to include guard rings around inputs (see Figure 45). These guards should be driven from a low-impedance source at the same voltage level as the common-mode input.

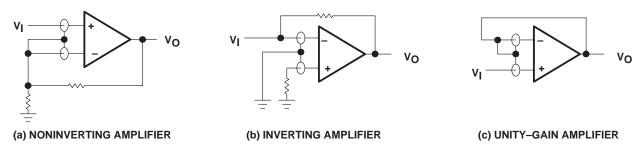


Figure 45. Use of Guard Rings

noise performance

The noise specifications in op amp circuits are greatly dependent on the current in the first-stage differential amplifier. The low input bias current requirments of these amplifiers result in a very low current noise. This feature makes the devices especially favorable over bipolar devices when using values of circuit impedance greater than 50 k Ω .

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